

# Post-Doctorate Position

## GaN Robustness

In the framework of the ICPEI/Nano 2022 project, Ampere laboratory will recruit a postdoctoral position to achieve studies on the robustness of GaN power devices.

The main target corresponds to lateral diodes on GaN (with a 2DEG channel) but some test could be applied to HEMT devices depending on the availability.

On diode devices the targets are

- Current Collapse measurement in switching condition
- HTRB (reverse state aging)
- Surge Current (in forward condition)
- Avalanche Robustness.

On HEMT devices the targets are

- HTGB/HTRB tests
- Short Circuit Robustness,
- Avalanche Robustness.

The effective achieved tests will depend on the obtained results, but the previous order is the preferable order.

During each test, some electrical characterization will be achieved to follow the possible aging.

The candidate must have some knowledge on Power Electronics. An experience in Power Semiconductor Device characterization or reliability test will be appreciated.

Duration: 12 months

Start: from March

Contact:

[Herve.Morel@insa-lyon.fr](mailto:Herve.Morel@insa-lyon.fr)